

TOSHIBA Transistor Silicon NPN Triple Diffused Type (Darlington)

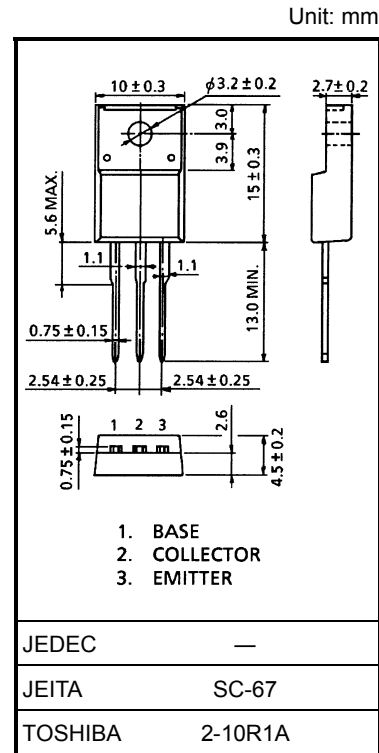
2SD2604

High-Power Switching Applications
 Hammer Drive, Pulse Motor Drive Applications

- High DC current gain: $h_{FE} = 2000$ (min)
- Low saturation voltage: $V_{CE(sat)} = 1.5$ V (max)

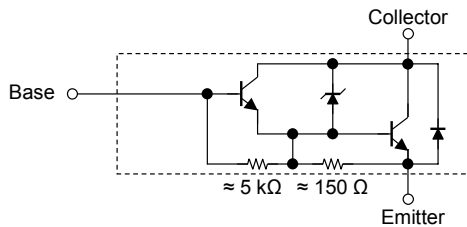
Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	95	V
Collector-emitter voltage		V_{CEO}	110 ± 15	V
Emitter-base voltage		V_{EBO}	5	V
Collector current	DC	I_C	5	A
	Pulse	I_{CP}	10	
Base current		I_B	0.7	A
Collector power dissipation	Ta = 25°C	P_C	2.0	W
	Tc = 25°C		20	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

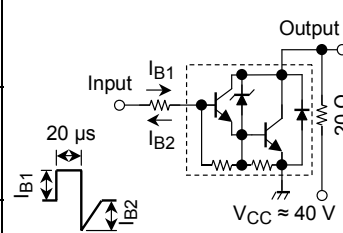


Weight: 1.7 g (typ.)

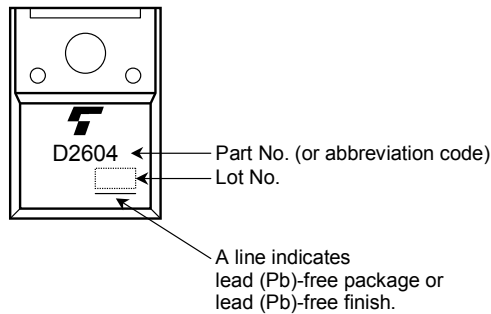
Equivalent Circuit

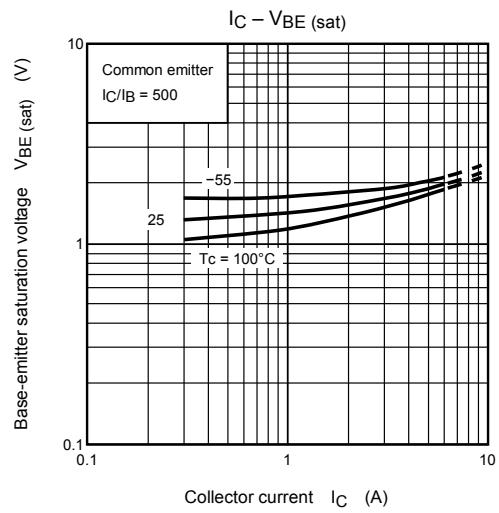
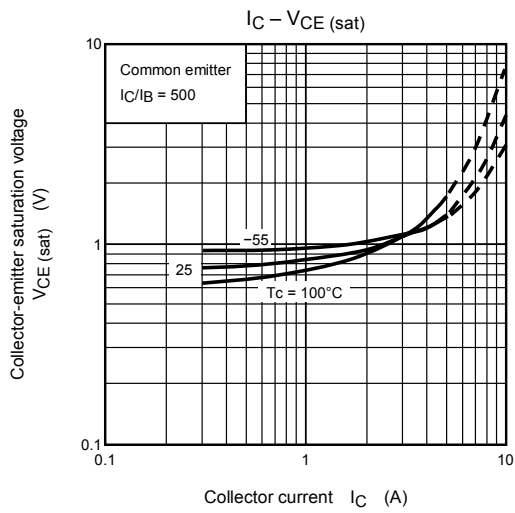
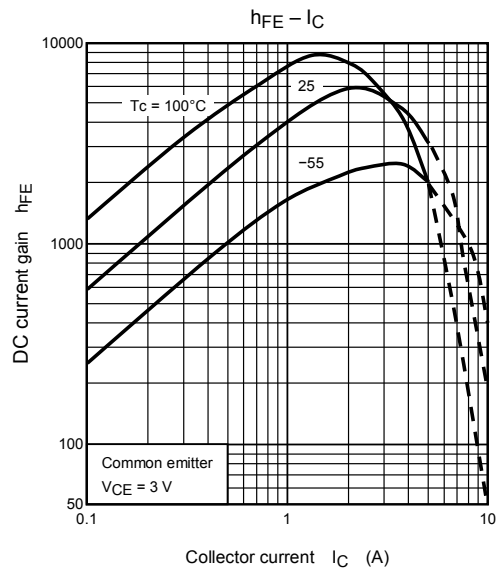
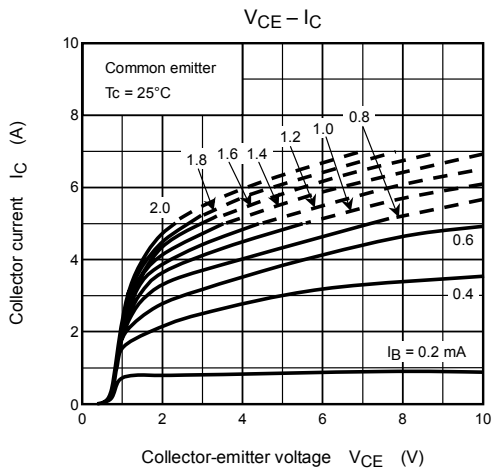


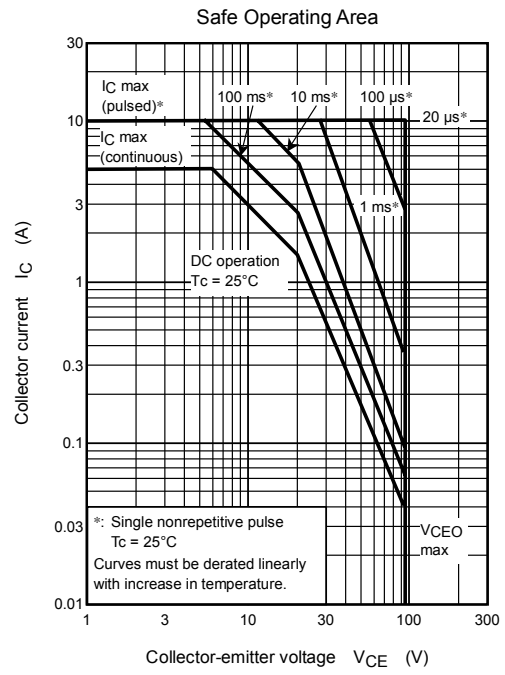
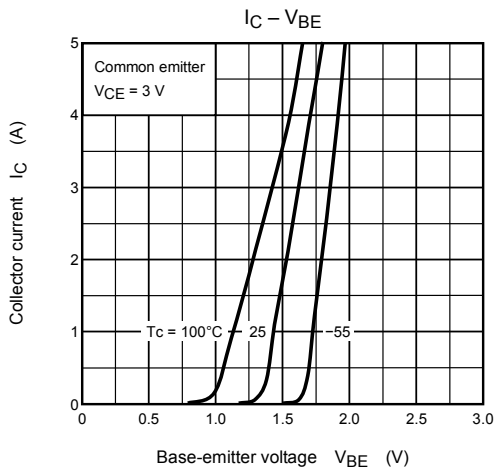
Electrical Characteristics (Tc = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	$V_{CB} = 90\text{ V}, I_E = 0$	—	—	100	μA
Emitter cut-off current		I_{EBO}	$V_{EB} = 6\text{ V}, I_C = 0$	0.75	—	3.0	μA
Collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	95	110	125	V
DC current gain		$h_{FE(1)}$	$V_{CE} = 3\text{ V}, I_C = 2\text{ A}$	2000	—	15000	
		$h_{FE(2)}$	$V_{CE} = 3\text{ V}, I_C = 5\text{ A}$	1000	—	—	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 2\text{ A}, I_B = 4\text{ mA}$	—	0.9	1.5	V
Base-emitter saturation voltage		$V_{BE(sat)}$	$I_C = 2\text{ A}, I_B = 4\text{ mA}$	—	1.5	2.5	V
Switching time	Turn-on time	t_{on}	 <p>$I_{B1} = -I_{B2} = 4\text{ mA}, \text{duty cycle} \leq 1\%$</p>	—	0.5	—	μs
	Storage time	t_{stg}		—	5.0	—	
	Fall time	t_f		—	0.7	—	

Marking







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